

## INFORMATION DISCLOSURE CITATION

Atty. Docket No.	04329.3139	Serial No.
Applicant	Mitsuaki IZUHA et al.	
Filing Date	September 12, 2003	Group:

U.S. PATENT DOCUMENTS							
Examiner Initial*	Document Number	Issue Date (Pub. Date)	Name	Class	Sub Class	Filing Date If Appropriate	
<i>SJL</i>	5,656,859	08/12/1997	Murakoshi et al.				
	5,770,512	06/23/1998	Murakoshi et al.				
<i>V</i>	2002/0130393 A1	(09/19/2002)	Takayanagi et al.				

FOREIGN PATENT DOCUMENTS						
	Document Number	Publication Date	Country	Class	Sub Class	Translation Yes or No
<i>SJL</i>	9-139511	05/27/1997	Japan			No
<i>SJL</i>	3219996	08/10/2001	Japan			No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
<i>SJL</i>	Ku et al.; "HIGH PERFORMANCE pMOSFETs WITH Ni(SixGe <sub>1-x</sub> )/POLY-Si <sub>0.8</sub> Ge <sub>0.2</sub> GATE"; Symposium on VSLI Technology Digest of Technical Papers, (2000)

Examiner	<i>SJL</i>	Date Considered	<i>12/27/05</i>
*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.			
Form PTO 1449		Patent and Trademark Office - U.S. Department of Commerce	



OMB No. 0651-0011

INFORMATION DISCLOSURE CITATION

Atty. Docket No.	4329.3139	Appln. No.	10/660,555
Applicant	Izuha et al.		
Filing Date	September 12, 2003	Group:	Unknown

U.S. PATENT DOCUMENTS

Examiner Initial*	Document Number	Issue Date	Name	Class	Sub Class	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS

	Document Number	Publication Date	Country	Class	Sub Class	Translation Yes or No
<i>SJL</i>	11-214680	8/6/99	Japan			Abstract

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>SJL</i>	Maa et al., "Stability Improvement of Nickel Silicide with Co Interlayer on Si, Polysilicon and SiGe," Mat. Res. Soc. Symp. Proc. (2001), 670:K6.9.1-K6.9.6
<i>SJL</i>	Wang et al., "Silicide formation and stability of Ti/SiGe and Co/SiGe," Thin Solid Films (1995), pp. 555-560

Examiner	<i>SJL</i>	Date Considered	<i>12/07/03</i>
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\*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

IDS Form PTO/SB/08: Substitute for form 1449A/PTO				<b>Complete if Known</b>													
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(Use as many sheets as necessary)</i>				<table border="1"> <tr> <td>Application Number</td> <td>10/660,555</td> </tr> <tr> <td>Filing Date</td> <td>September 12, 2003</td> </tr> <tr> <td>First Named Inventor</td> <td>Mitsuaki Izuha</td> </tr> <tr> <td>Art Unit</td> <td>2811</td> </tr> <tr> <td>Examiner Name</td> <td>VU, Quang D.</td> </tr> <tr> <td>Attorney Docket Number</td> <td>4329.3139</td> </tr> </table>		Application Number	10/660,555	Filing Date	September 12, 2003	First Named Inventor	Mitsuaki Izuha	Art Unit	2811	Examiner Name	VU, Quang D.	Attorney Docket Number	4329.3139
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Art Unit	2811																
Examiner Name	VU, Quang D.																
Attorney Docket Number	4329.3139																
Sheet	1	of	1														

## **U.S. PATENTS AND PUBLISHED U.S. PATENT APPLICATIONS**

**Note: Copies of the U.S. Patent Documents are not Required in IDS filed after October 21, 2004**

## **FOREIGN PATENT DOCUMENTS**

Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	Translation <sup>6</sup>
		JP 2000-150669		Not translated		

## **NON PATENT LITERATURE DOCUMENTS**

Examiner Initials	Cite No. <sup>4</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	Translation <sup>5</sup>
<i>SP</i>		Japanese Patent Office Notification of Reasons for Rejection and English translation thereof.	
	(Appln. #2002-268970)		
<i>SP</i>		Ja-Hum Ku et al., "High Performance pMOSFETs with Ni(Si <sub>x</sub> Ge <sub>1-x</sub> )/Poly-Si <sub>0.8</sub> Ge <sub>0.2</sub> Gate," 2000 Symposium on VLSI Technology Digest of Technical Papers, 2000, pp. 114 to 115.	
<i>SFe</i>		H. B. Zhao et al., "Interfacial reactions of Ni on Si <sub>1-x</sub> Ge <sub>x</sub> (x=0.2, 0.3) at low temperature by rapid thermal annealing," Journal of Applied Physics, July 1, 2002, Volume 92, Number 1, pp. 214-217.	

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